

Dimiter Alexandrov

List of Publications by Year in descending order

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Version: 2024-02-01

17
papers

89
citations

1684188
5
h-index

1720034
7
g-index

17
all docs

17
docs citations

17
times ranked

92
citing authors

#	ARTICLE	IF	CITATIONS
1	Absorption and photoluminescence features caused by defects in InN. Journal of Crystal Growth, 2004, 269, 77-86.	1.5	29
2	Excitons of the structure in wurtzite $\text{In}_x\text{Ga}_{1-x}\text{N}$ and their properties. Journal of Crystal Growth, 2002, 246, 325-340.	1.5	15
3	InN grown by migration enhanced afterglow (MEAglow). Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 41-44.	1.8	15
4	Energy band gaps of InN containing oxygen and of the $\text{In}_x\text{Al}_{1-x}\text{N}$ interface layer formed during InN film growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 954.	2.1	12
5	Impedance Study of GaN and InGaN Semiconductor Anion Selective Electrodes. Electroanalysis, 2008, 20, 789-796.	2.9	7
6	Energy band gap and optical properties of non-stoichiometric InN_x theory and experiment. Journal of Crystal Growth, 2006, 288, 261-267.	1.5	5
7	Evaluation of GaN and $\text{In}_{0.2}\text{Ga}_{0.8}\text{N}$ Semiconductors as Potentiometric Anion Selective Electrodes. Electroanalysis, 2007, 19, 1799-1806.	2.9	4
8	Low temperature epitaxial deposition of GaN on LTCC substrates. , 2017, , .		1
9	Low energy nuclear fusion reactions in solids: Experiments. International Journal of Energy Research, 2021, 45, 12234-12246.	4.5	1
10	Excitons of the Structure in Zinc-Blende $\text{In}_x\text{Ga}_{1-x}\text{N}$ and their Properties. Materials Research Society Symposia Proceedings, 2002, 743, L11.11.1.	0.1	0
11	Electron Band Structure of MnGaN. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
12	Structure of Isolated Oxygen Impurity States in InN. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
13	Dielectric susceptibility of InN and related alloys. Journal of Materials Science: Materials in Electronics, 2007, 18, 123-126.	2.2	0
14	INTERACTION BETWEEN POSITIVE HYDROGEN IONS AND ELECTRONS LOCATED IN INDIUM NITRIDE CONTAINING OXYGEN IMPURITIES. Nano, 2008, 03, 387-390.	1.0	0
15	Dependence of the magnetic properties of MnGaN epitaxial layers on external electrical field. Open Chemistry, 2009, 7, 175-178.	1.9	0
16	Modeling of metal-oxide-semiconductor capacitor on Indium Gallium Nitride 1- channel model. , 2012, , .		0
17	Low temperature growth of InAlN on epitaxially grown SiC/Si (111) wafers. , 2017, , .		0